Silicon Carbide (SiC) MOSFET - EliteSiC, 32 mohm, 650 V, M3S, D2PAK-7L

NTBG032N065M3S

- Ω
-
-
-
-
  –
-

(T_J = 25°C unless otherwise noted)

Drain−to−Source Voltage	V_{DSS}	650	V
Gate−to−Source Voltage	V_{GS}	−8/+22	

μs

		I_{DM}	156	A
Continuous Source−Drain Current (Body Diode)	T_C = 25°C, V_{GS} = −3 V	I_S	30	
	T_C = 100°C, V_{GS} = −3 V		17	
Pulsed Source−Drain Current (Body Diode) (Note 1)	T_C = 25°C, V_{GS} = −3 V, t_P = 100 μs	I_{SM}	127	
Single Pulse Avalanche Energy (Note 2)	I_{LPK} = 16.7 A, L = 1 mH	E_{AS}		

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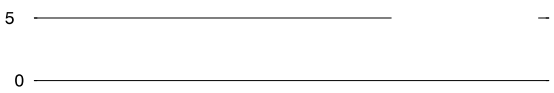
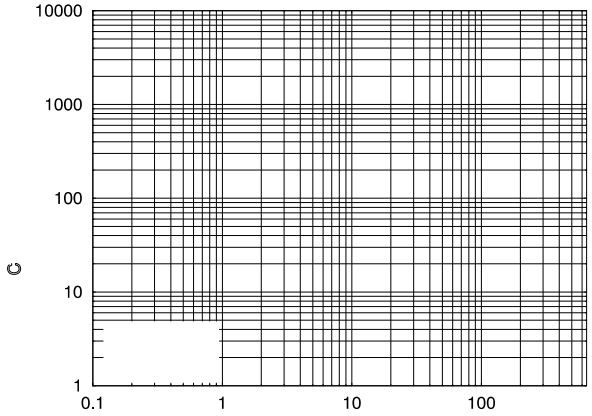
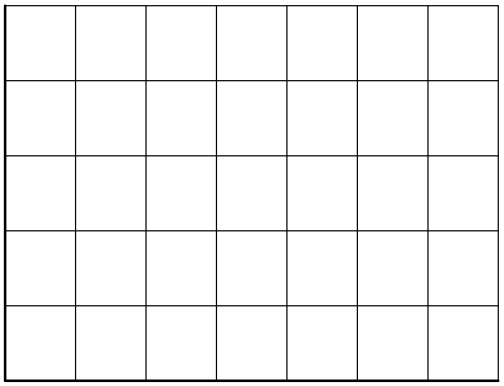
Publication Order Number:

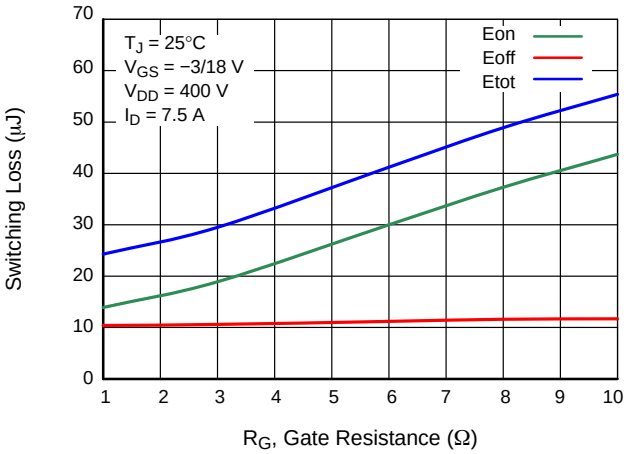
(T_J = 25°C unless otherwise specified) (continued)

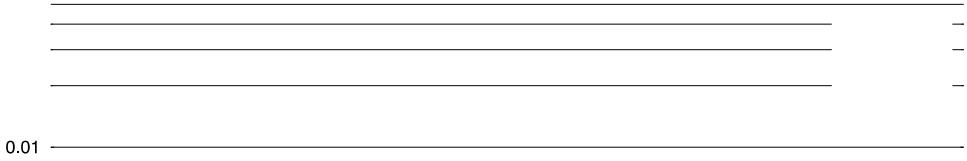
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −3/18 V, I_D = 15 A, V_{DD}




10000
1000
100
10
1
0.1
1
10
100

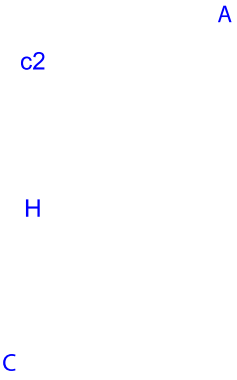



70
60
50
40
30
20
10
0
Switching Loss (μJ)
T_J = 25°C
V_{GS} = −3/18 V
V_{DD} = 400 V
I_D = 7.5 A
Eon
Eoff
Etot
1
2
3
4
5
6
7
8
9
10
R_G, Gate Resistance (Ω)


0.01

D^{2}PAK7 (TO−263−7L HV)
CASE 418BJ
ISSUE B

DATE 16 AUG 2019



GENERIC
MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.